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Yoshizawa

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(54) **METHOD FOR PRODUCING OSCILLATOR**

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B81C 1/00 (2006.01)

(52) **U.S. Cl.**

CPC **B81C 1/00158** (2013.01)

USPC **438/52**

(58) **Field of Classification Search**

None

See application file for complete search history.

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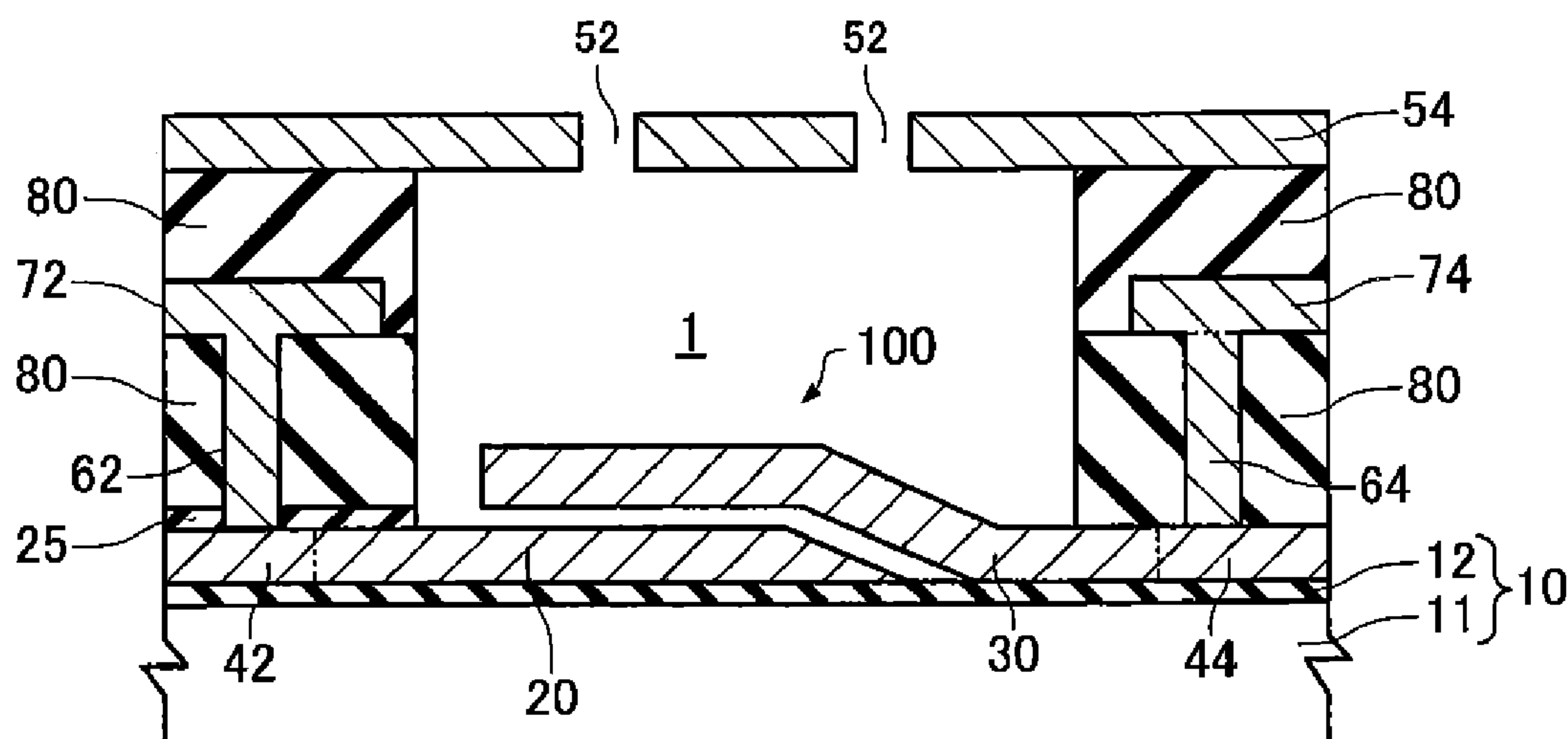
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(57) **ABSTRACT**

A method for producing an oscillator includes: (a) forming a first layer on a substrate; (b) ion implanting a first impurity into a first region of the first layer; (c) forming a first electrode having a tapered plane on a side surface thereof by patterning the first layer; (d) forming a sacrificial layer on the first electrode and on the tapered plane of the first electrode; (e) forming a second electrode on the substrate and the sacrificial layer; and (f) removing the sacrificial layer. The step (b) is performed so that the concentration of the first impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode.

7 Claims, 6 Drawing Sheets



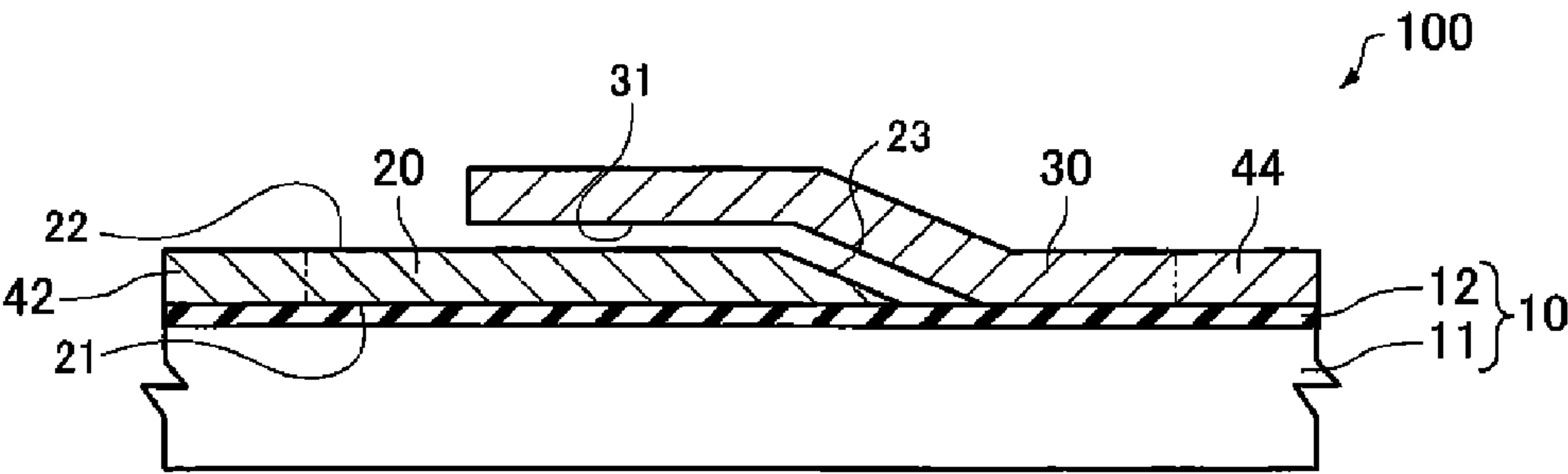


FIG. 1

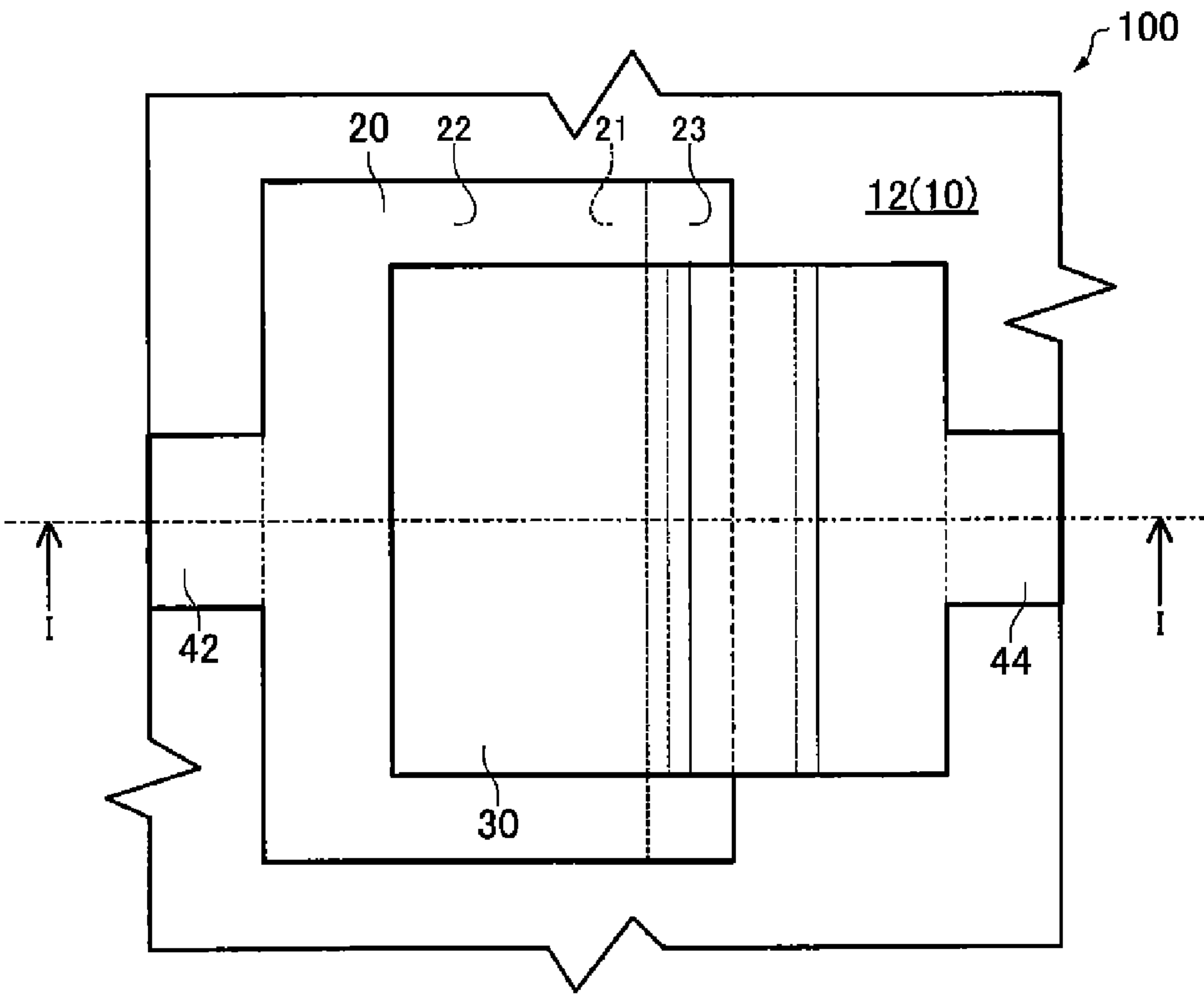


FIG. 2

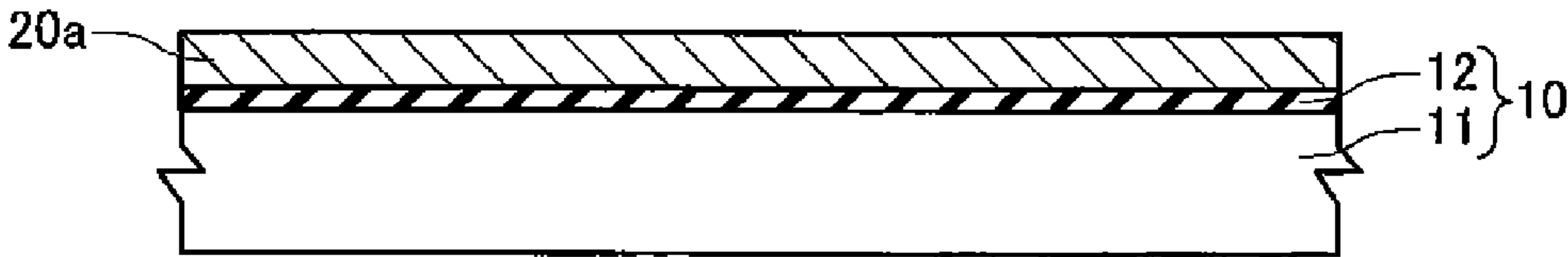


FIG. 3

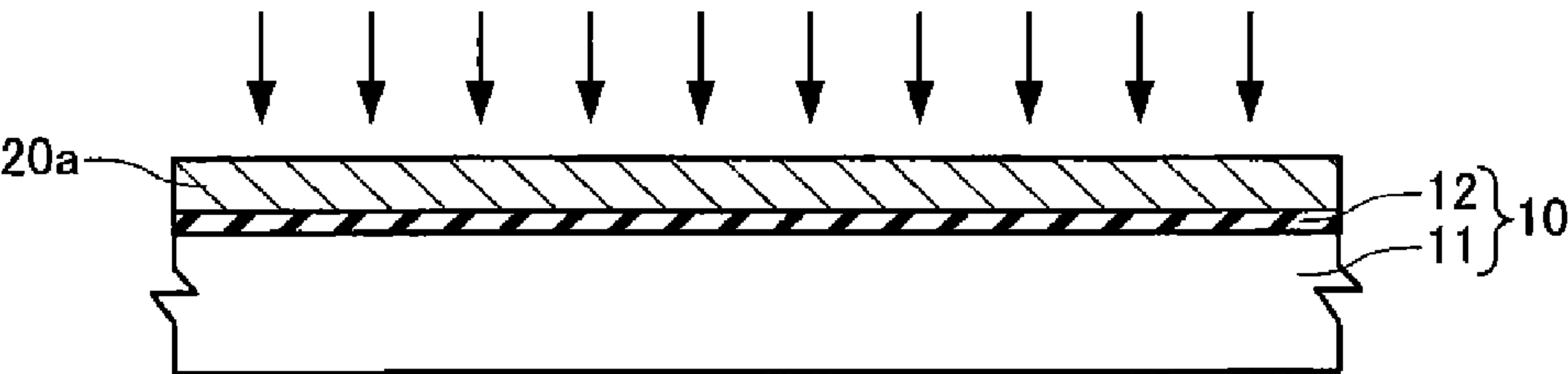


FIG. 4

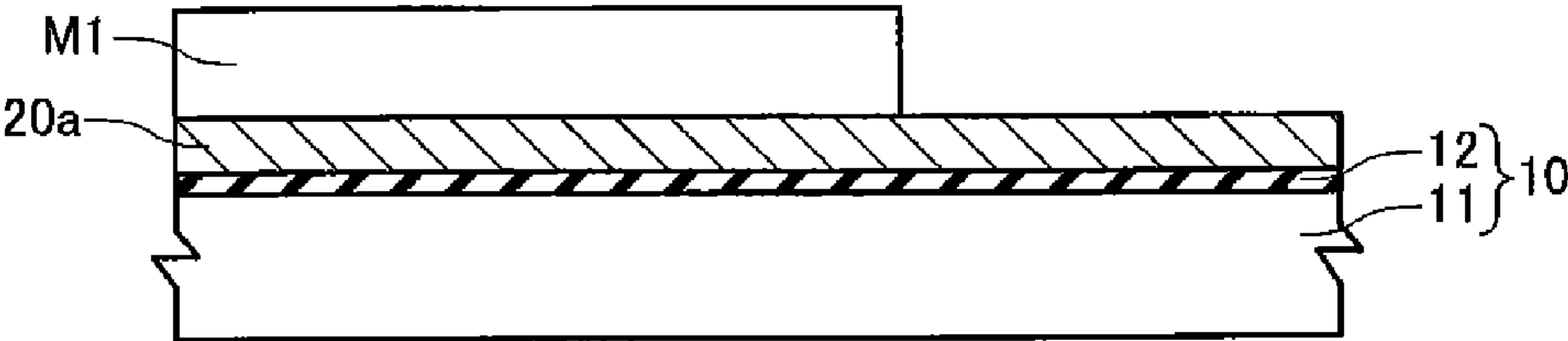


FIG. 5

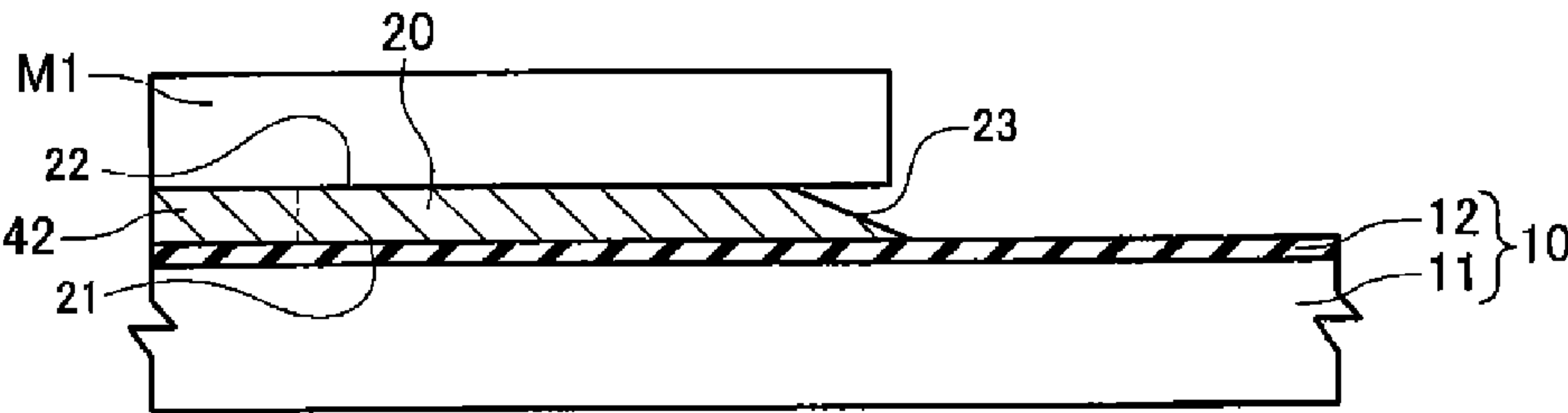


FIG. 6

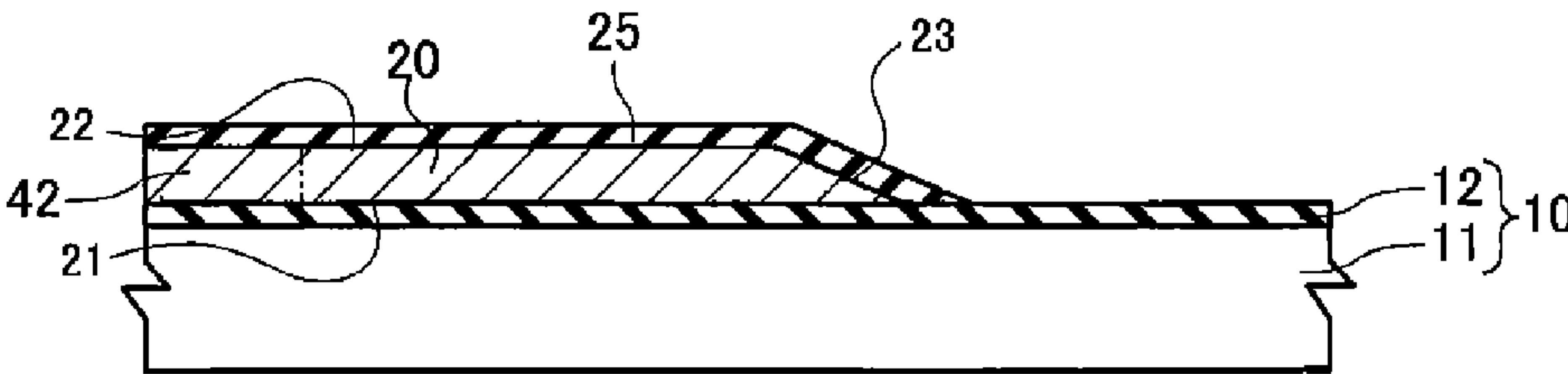


FIG. 7

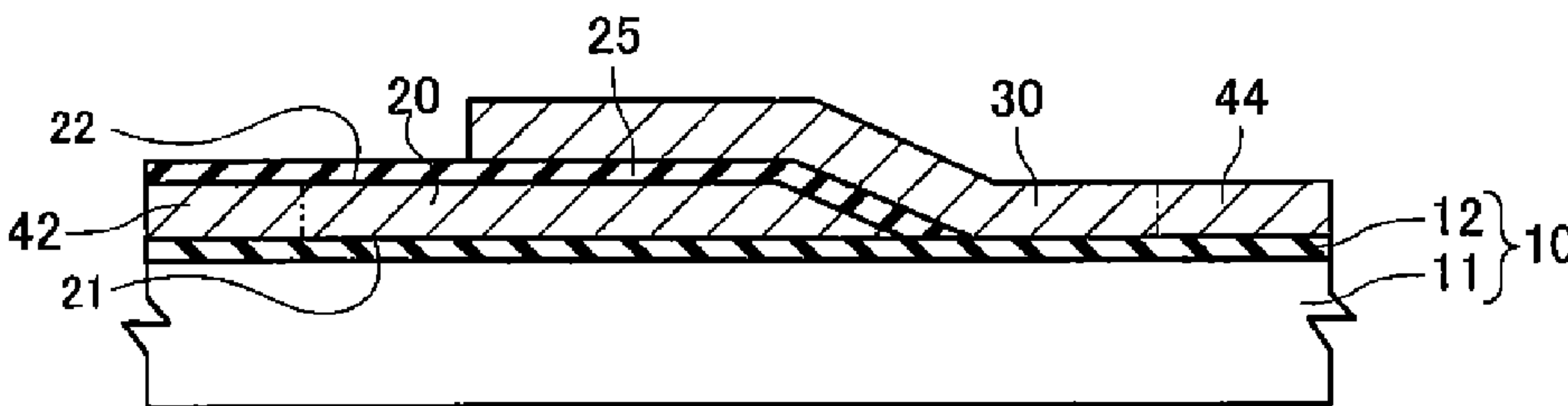


FIG. 8

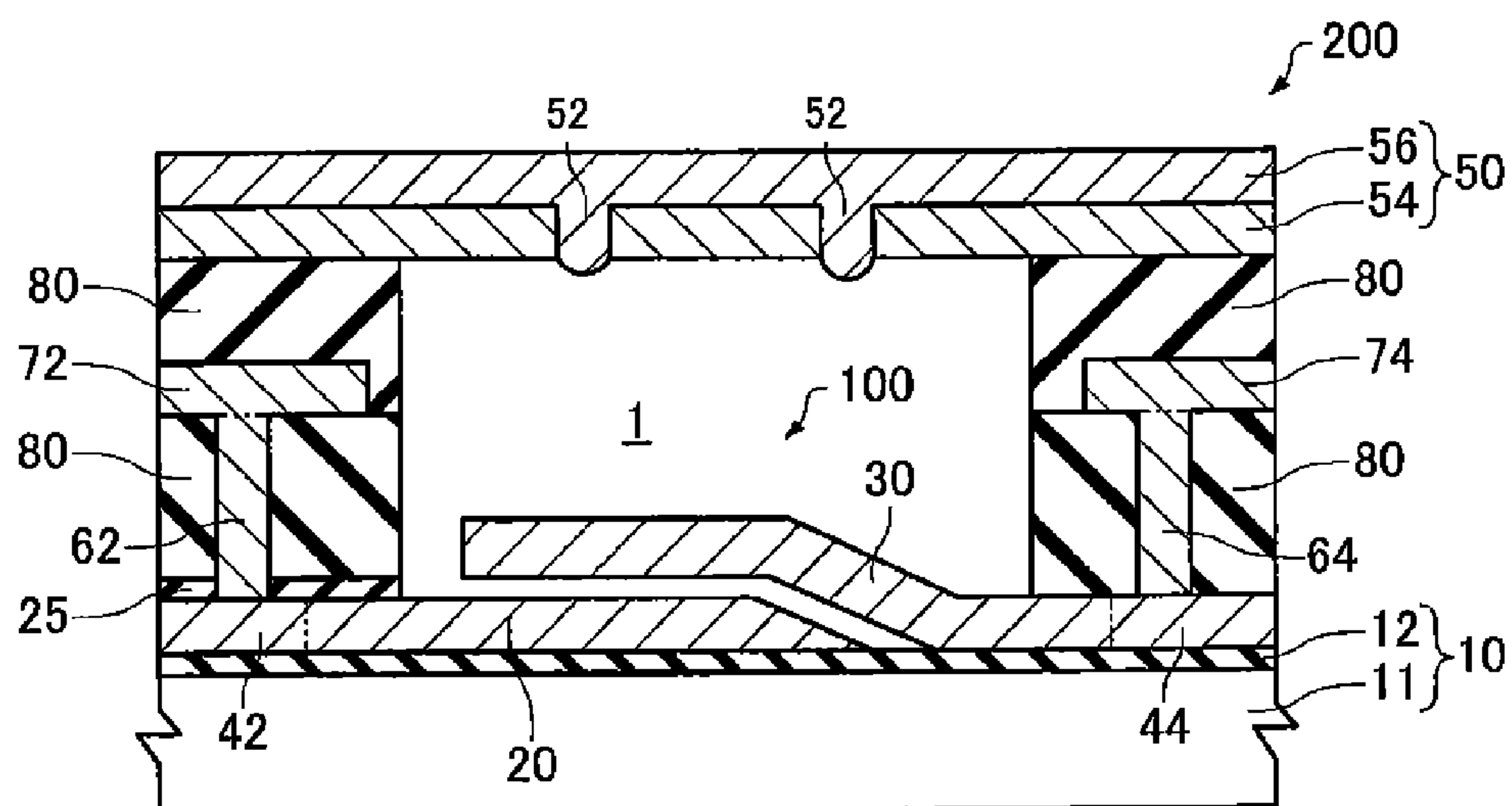


FIG. 9

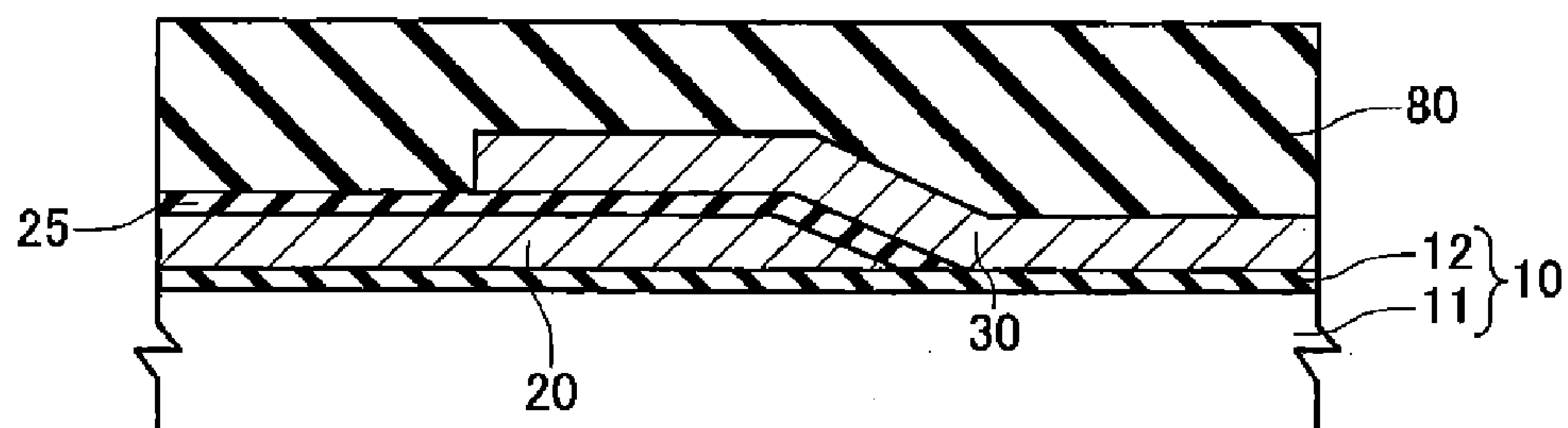


FIG. 10

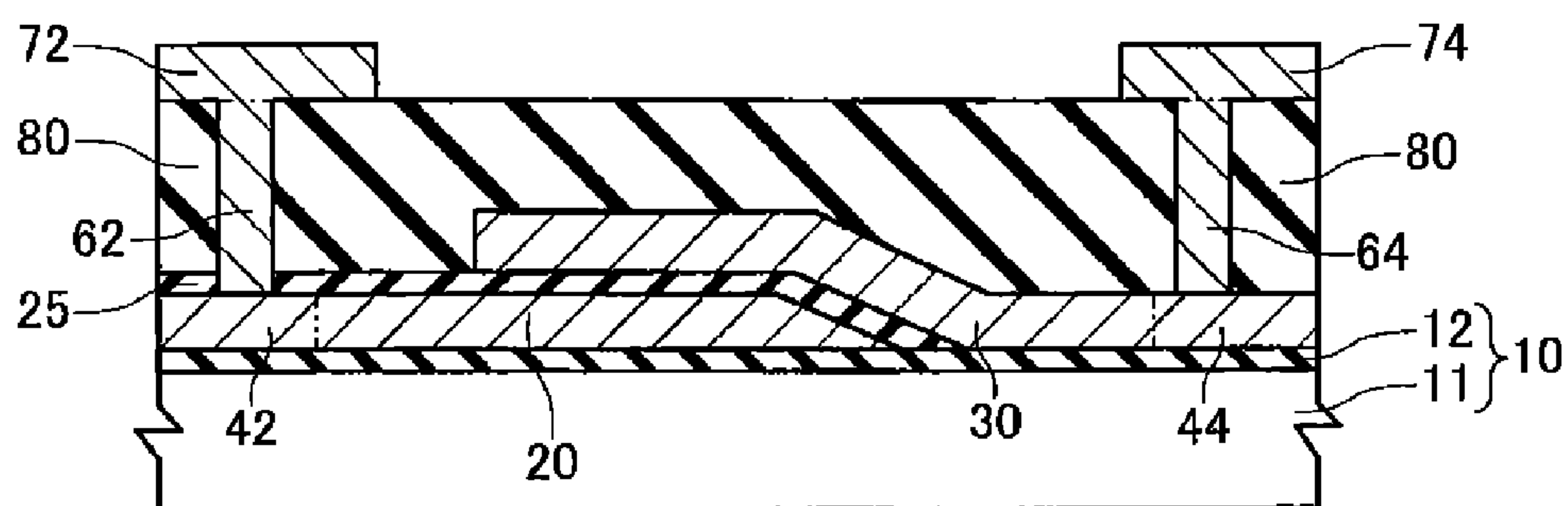


FIG. 11

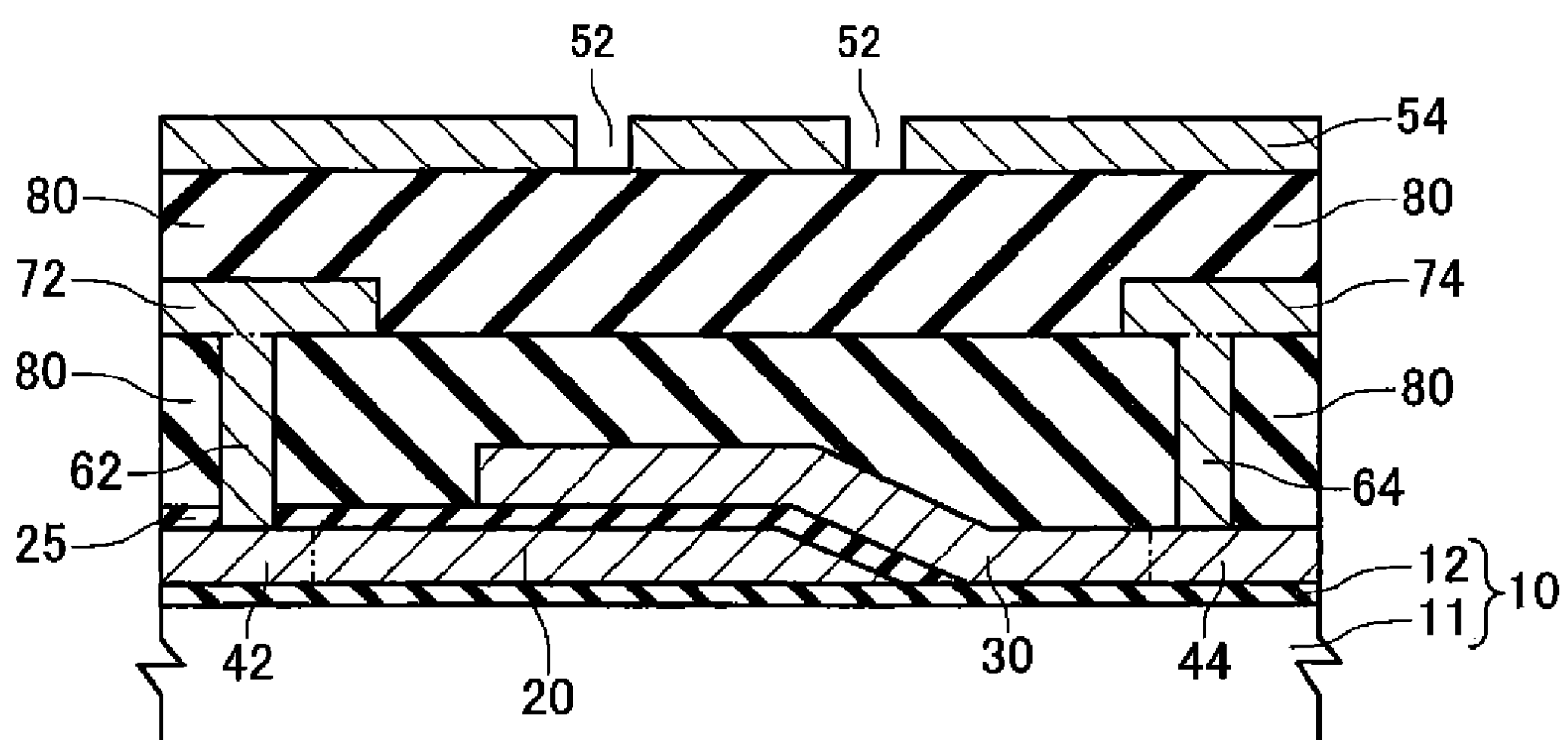


FIG. 12

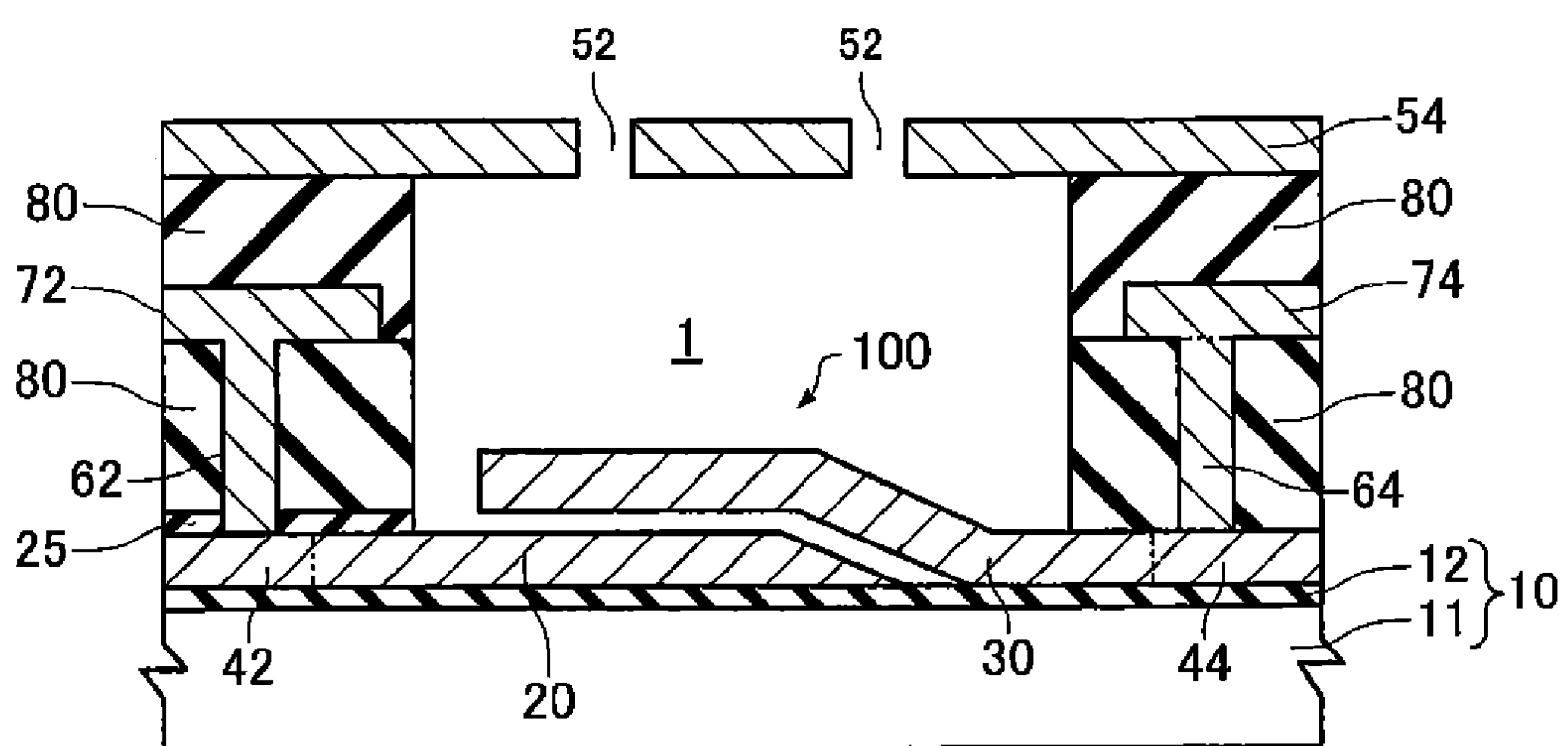


FIG. 13

MEASUREMENT RESULTS OF CONCENTRATION OF PHOSPHORUS BY SIMS
(Y AXIS REPRESENTS LINEAR SCALE)

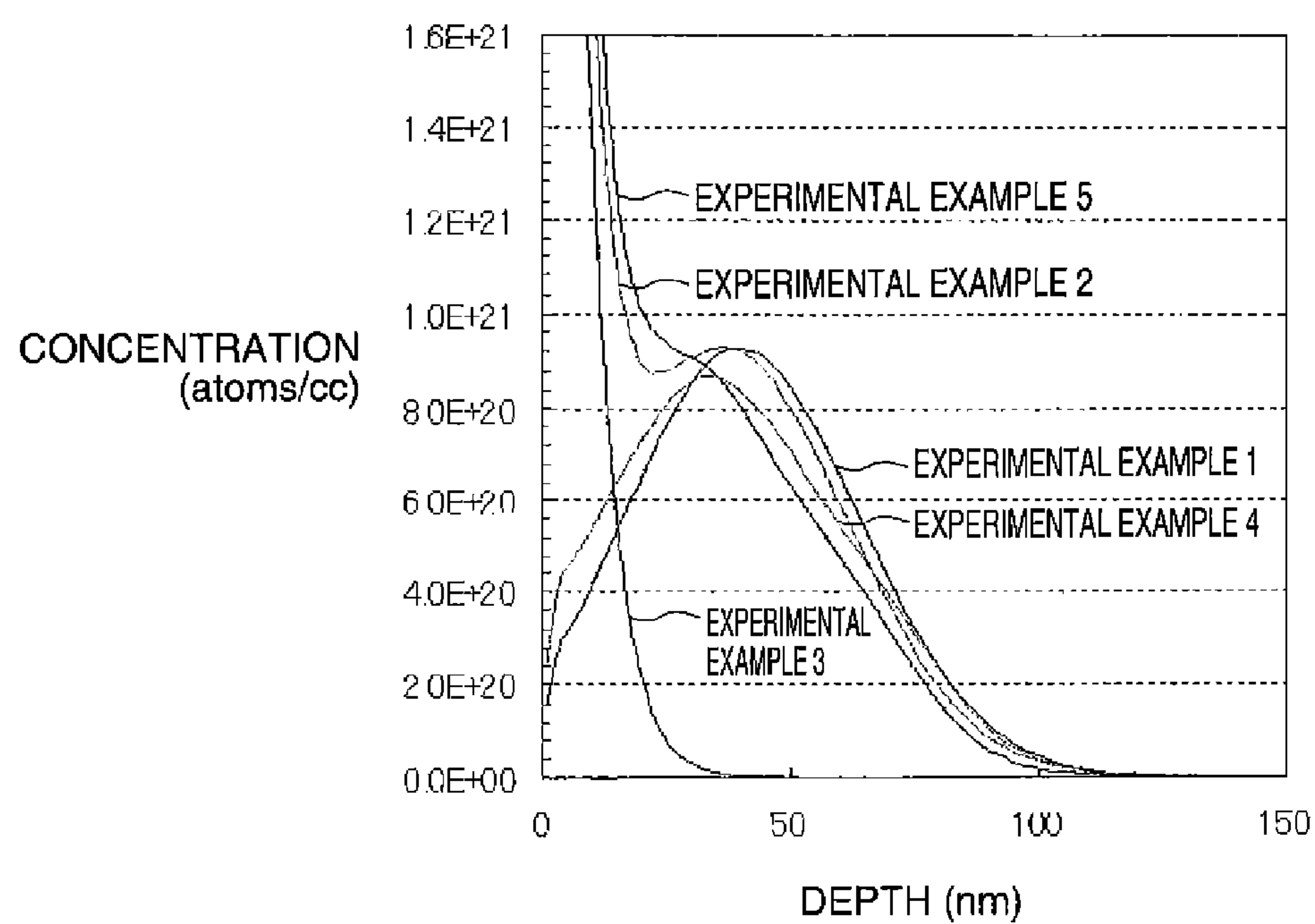


FIG. 14

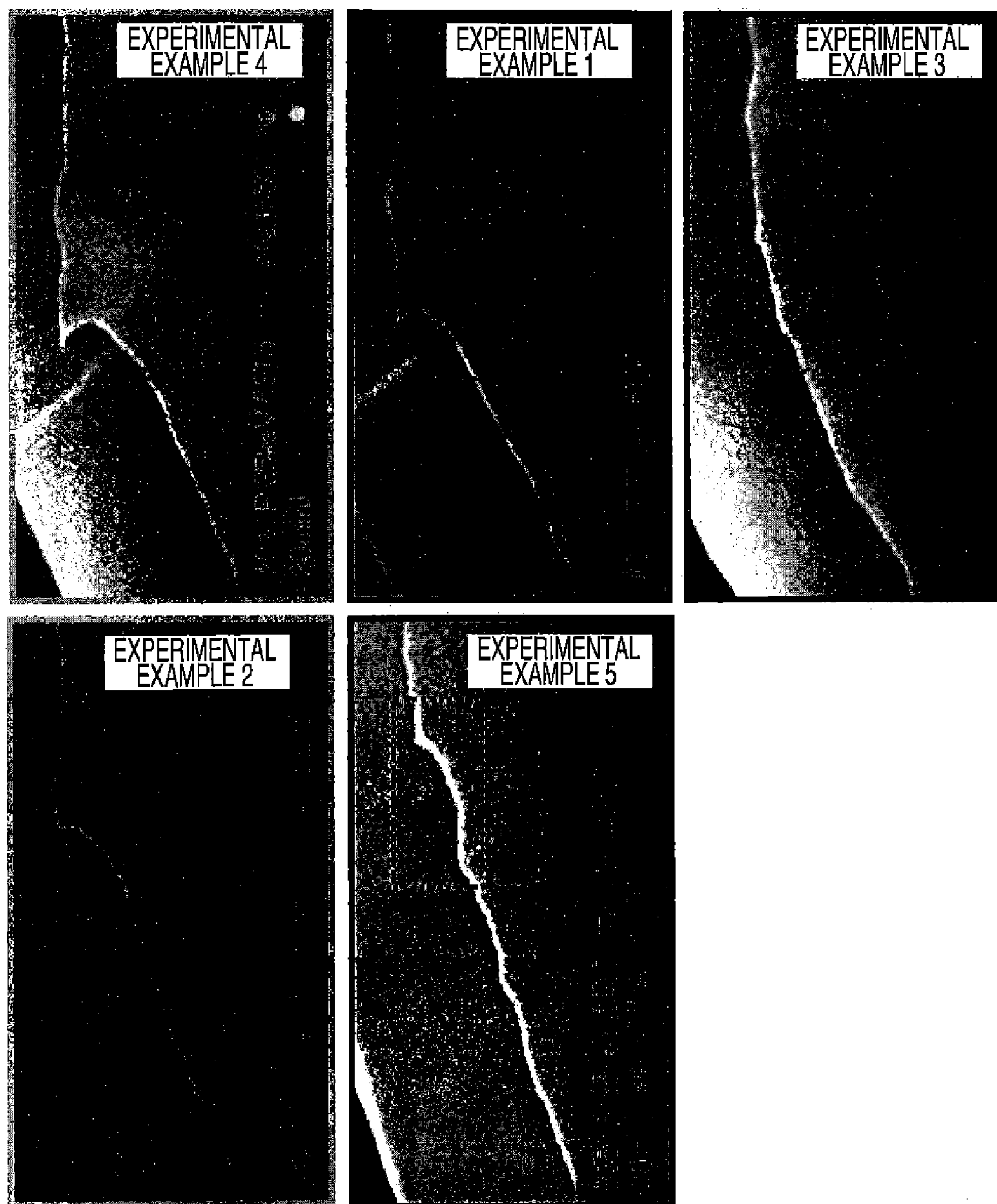


FIG. 15

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METHOD FOR PRODUCING OSCILLATOR

The entire disclosure of Japanese Patent Application No. 2012-267814, filed Dec. 7, 2012 is expressly incorporated by reference herein.

BACKGROUND**1. Technical Field**

The present invention relates to a method for producing an oscillator.

2. Related Art

There has been an increase in the development of technologies related to MEMS (Micro-Electro-Mechanical System) in the field of acceleration sensors and video devices. MEMS refers to a very small functional device produced using a semiconductor production technique, and is produced on the basis of a microprocessing technique in the semiconductor production of the related art. Examples of the functional device to be produced include microoscillators, microsen-

sors, and microactuators, and the functional device exhibits a variety of functions by oscillation, deformation, or other action of a microstructure (see, for example, JP-A-2007-160495). In the case of a functional device which detects a variety of physical amounts by oscillating or deforming a microstructure, the structure may be essentially damaged due to the oscillation or deformation. In particular, to a bend region or a flexure region of an oscillator or the like, stress is repeatedly applied, and therefore, it is desirable to design the structure so that such stress does not concentrate on a specific region as much as possible. Further, for example, in the case where a groove, a hole, a defect, or the like is formed in the structure, stress concentration due to bend or flexure is liable to occur particularly prominently in the region where a groove, a hole, a defect, or the like is formed.

In the case where such an oscillator or the like is formed by a microprocessing technique of the related art in the semiconductor production, the shape after processing may be sometimes problematic, although it is not problematic in the semiconductor production. For example, in the case where an electrode is formed on a substrate, when it is formed by a microprocessing technique of the related art, a small angular portion is sometimes formed in the vicinity of an edge of the electrode. Such an angular portion is not a big problem in a semiconductor device having no bend region or flexure region. However, in the case where an oscillator or the like having a fixed electrode and a movable electrode disposed to face the fixed electrode is produced, for example, if a small angular portion is formed on the fixed electrode, an inappropriate groove derived from the angular portion of the fixed electrode is sometimes formed on the movable electrode to be formed after forming the fixed electrode. In this case, stress concentration is liable to occur in the groove of the movable electrode corresponding to the bend region or the flexure region of the oscillator, and the reliability of the oscillator may be deteriorated. Further, a short circuit may occur due to the contact between the angular portion of the fixed electrode and the movable electrode.

SUMMARY

An advantage of some aspects of the invention is to provide a method for producing an oscillator in which a region on which stress concentrates is reduced so as to achieve high reliability, and the occurrence of short circuit between electrodes is suppressed.

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The invention can be implemented as the following forms or application examples.

APPLICATION EXAMPLE 1

This application example is directed to a method for producing an oscillator including: (a) forming a first layer on a substrate; (b) ion implanting a first impurity into a first region of the first layer; (c) forming a first electrode having a tapered plane on a side surface thereof by patterning the first layer; (d) forming a sacrificial layer on the first electrode and on the tapered plane of the first electrode; (e) forming a second electrode on the substrate and the sacrificial layer so that the second electrode is disposed to face at least a part of the upper surface of the first electrode and the tapered plane of the first electrode; and (f) removing the sacrificial layer, wherein the step (b) is performed so that the concentration of the first impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode.

According to the method for producing an oscillator of this application example, a highly reliable oscillator, in which an angular portion is hardly formed on the first electrode, a groove acting as an unexpected stress concentration point is hardly formed on a surface of the second electrode facing the first electrode, the damage to the second electrode which is deformed by an electrostatic force between the first electrode and the second electrode is suppressed, and the occurrence of short circuit between the electrodes is suppressed can be produced.

APPLICATION EXAMPLE 2

Application Example 1 may be configured such that the method further includes (g) ion implanting a second impurity into a second region of the first layer between the step (a) and the step (b), or between the step (b) and the step (c), and the step (g) is performed so that the second region is located closer to the substrate than the first region, at least a part of the second region overlaps with the first region, and the combined concentration of the first impurity and the second impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode.

According to the method for producing an oscillator of this application example, an oscillator in which the damage to the electrode and the occurrence of short circuit between the electrodes are suppressed can be produced, and further, the control of the resistance of the first electrode can be easily performed.

APPLICATION EXAMPLE 3

Application Example 1 or 2 may be configured such that the method further includes, between the step (a) and the step (b), or between the step (b) and the step (c): (g) ion implanting a second impurity into a second region of the first layer; and (h) heating the first layer, and the step (g) is performed so that the second region is located closer to the substrate than the first region, the step (h) is performed so that at least a part of the second impurity is diffused in the first region, and the step (g) and the step (h) is performed so that the combined concentration of the first impurity and the second impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode.

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According to the method for producing an oscillator of this application example, an oscillator in which the damage to the electrode and the occurrence of short circuit between the electrodes are suppressed can be produced, and further, the control of the resistance of the first electrode and the activation of the impurity can be easily performed.

APPLICATION EXAMPLE 4

Any of Application Examples 1 to 3 may be configured such that the first impurity and the second impurity have the same conductivity type.

APPLICATION EXAMPLE 5

Any of Application Examples 1 to 4 may be configured such that the first layer is composed of a semiconductor layer, and in the step of forming the sacrificial layer, the semiconductor layer is formed by thermal oxidation.

According to the method for producing an oscillator of this application example, an oscillator in which the damage to the electrode and the occurrence of short circuit between the electrodes are suppressed can be produced, and further, since the distance between the first electrode and the second electrode can be made constant, and therefore, an oscillator in which the occurrence of short circuit between the electrodes is further suppressed can be produced.

APPLICATION EXAMPLE 6

Application Example 5 may be configured such that the first layer is composed of a polycrystalline silicon layer.

APPLICATION EXAMPLE 7

Any of Application Examples 1 to 6 may be configured such that the step of patterning the first layer includes: forming a resist pattern on the first layer; and etching the first layer by using the resist pattern as a mask, and in the etching step, etching is allowed to proceed on the lower surface side of the resist pattern.

According to the method for producing an oscillator of this application example, an oscillator in which the controllability of the tapered shape is favorable and further, damage hardly occurs can be produced.

BRIEF DESCRIPTION OF THE DRAWINGS

The invention will be described with reference to the accompanying drawings, wherein like numbers reference like elements.

FIG. 1 is a schematic cross-sectional view showing an oscillator according to an embodiment.

FIG. 2 is a schematic plan view showing the oscillator according to the embodiment.

FIG. 3 is a schematic cross-sectional view showing one step of a method for producing an oscillator according to an embodiment.

FIG. 4 is a schematic cross-sectional view showing one step of the method for producing an oscillator according to the embodiment.

FIG. 5 is a schematic cross-sectional view showing one step of the method for producing an oscillator according to the embodiment.

FIG. 6 is a schematic cross-sectional view showing one step of the method for producing an oscillator according to the embodiment.

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FIG. 7 is a schematic cross-sectional view showing one step of the method for producing an oscillator according to the embodiment.

FIG. 8 is a schematic cross-sectional view showing one step of the method for producing an oscillator according to the embodiment.

FIG. 9 is a schematic cross-sectional view showing an electronic device according to an embodiment.

FIG. 10 is a schematic cross-sectional view showing one step of a method for producing an electronic device according to an embodiment.

FIG. 11 is a schematic cross-sectional view showing one step of the method for producing an electronic device according to the embodiment.

FIG. 12 is a schematic cross-sectional view showing one step of the method for producing an electronic device according to the embodiment.

FIG. 13 is a schematic cross-sectional view showing one step of the method for producing an electronic device according to the embodiment.

FIG. 14 is a graph showing the SIMS measurement results of experimental examples.

FIG. 15 is a graph showing the SEM observation results of experimental examples.

DESCRIPTION OF EXEMPLARY EMBODIMENTS

Hereinafter, several embodiments of the invention will be described. The embodiments described below are mere examples of the invention. The invention is by no means limited to the embodiments described below and encompasses various modifications carried out within the scope in which the gist of the invention is not changed. Incidentally, not all structures described below are necessarily essential components of the invention.

1. Oscillator

An oscillator **100** of this embodiment includes a substrate **10**, a first electrode **20**, which is formed on the substrate **10** and is composed of polycrystalline silicon doped with an impurity, and a second electrode **30**, which is disposed above and spaced apart from the first electrode **20**, and is deformed by an electrostatic force between the first electrode **20** and the second electrode **30**. The impurity concentration in the first electrode **20** monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode **20**.

FIG. 1 is a schematic cross-sectional view showing the oscillator **100** of this embodiment. FIG. 2 is a schematic plan view showing the oscillator **100** of this embodiment. The cross section cut along the I-I line in FIG. 2 corresponds to FIG. 1.

1.1 Substrate

As the substrate **10**, a single crystalline semiconductor substrate, for example, a substrate made of silicon (Si), gallium arsenide (GaAs), or the like can be used. Further, as the substrate **10**, any of a variety of substrates such as a ceramic substrate, a glass substrate, a sapphire substrate, and a synthetic resin substrate may be used. The substrate **10** is preferably a single crystalline silicon substrate. The thickness of the substrate **10** is, for example, from 100 to 400 μm .

The substrate **10** may have an insulating underlayer **12** as shown in the drawing. In the example shown in the drawing, the substrate **10** is configured such that an underlayer **12** is

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formed on the surface of a silicon substrate **11**. Examples of the material of the underlayer **12** include silicon nitride (Si_3N_4). Further, the underlayer **12** may be used as an etching stopper layer in the case where a hollow for accommodating the oscillator **100** is formed. In addition, in the substrate **10**, a trench insulating layer, an LOCOS (Local Oxidation of Silicon) insulating layer, a semi-recess LOCOS insulating layer, or the like (not shown in the drawing) may be further formed under the underlayer **12**.

1.2 First Electrode

The first electrode **20** is formed on the substrate **10**. The shape of the first electrode **20** is not particularly limited, and is suitably designed according to the requirement for the function or sensitivity of the oscillator **100**. In the example shown in FIG. **2**, the first electrode **20** is formed in a rectangular shape in plan view and electrically connected to an integrally formed wiring **42**.

The first electrode **20** has a first plane **21** and a second plane **22**, both of which are in parallel with the substrate **10** and define the thickness of the first electrode **20**. The first plane **21** is a flat plane facing the substrate **10**, in other words, a lower surface of the first electrode **20**, and the second plane **22** is a flat plane located on the opposite side to the substrate **10**, in other words, an upper surface of the first electrode **20**. The outline of the first plane **21** in plan view is located outside the outline of the second plane **22** in plan view in at least a region where the first electrode **20** faces the second electrode **30**.

The first electrode **20** has a tapered plane **23** connecting between the first plane **21** and the second plane **22**. The tapered plane **23** is a plane which defines the thickness of the first electrode **20** so that the thickness thereof decreases toward the substrate **10** in at least a region where the first electrode **20** faces the second electrode **30**. The tapered plane **23** is drawn as a flat plane in the drawing, but may be a flat plane or a curved plane, and also may be a combination of these planes. The tapered plane **23** may be a continuous plane over the entire periphery of the first electrode **20** in plan view.

Here, for each of the first plane **21**, the second plane **22**, and the tapered plane **23**, the expression of "flat plane" is used, however, this expression does not mean that the first plane **21**, the second plane **22**, or the tapered plane **23** is smooth and does not have even slight irregularities. For example, the first plane **21**, the second plane **22**, or the tapered plane **23** sometimes has irregularities derived from an atom constituting the first electrode **20**, irregularities derived from a secondary structure (such as a particle, a particle aggregate, or a particle boundary) of a substance constituting the first electrode **20**, or the like, and therefore is not an exact flat plane from a microscopic viewpoint in some cases. However, there is a condition in which even in such cases, such irregularities become less noticeable from a more macroscopic viewpoint, and therefore are observed to such an extent that the first plane **21**, the second plane **22**, or the tapered plane **23** is allowed to be referred to as a flat plane. Accordingly, in this specification, if a plane can be recognized as a flat plane from such a more macroscopic viewpoint, this plane shall be referred to as a flat plane. More specifically, for example, when the cross section of the first plane **21**, the second plane **22**, or the tapered plane **23** is observed by a general-purpose scanning electron microscope having a resolution of about 5 nm, if noticeable irregularities are not observed, the plane shall be referred to as a flat plane.

A distance between the first plane **21** and the second plane **22** of the first electrode **20** (a thickness defined by the first plane **21** and the second plane **22**) can be set to 100 nm or more and 10 μm or less. The thickness of a portion defined by

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the first plane **21** and the tapered plane **23** of the first electrode **20** may be gradually decreased along the direction toward the second electrode **30**.

The function of the first electrode **20** in the oscillator **100** of this embodiment is to serve as one of the electrodes constituting a capacitor by being paired with the second electrode **30**.

In this embodiment, the first electrode **20** is composed of polycrystalline silicon doped with an impurity. The first electrode may be composed of a semiconductor material such as amorphous silicon or single crystalline silicon. Examples of the impurity include arsenic (As), phosphorus (P), and boron (B). The impurity can be introduced by, for example, ion implantation. The impurity may be activated by a heat treatment.

The impurity concentration in the first electrode **20** monotonically decreases from the upper surface (the second plane **22**) side to the lower surface (the first plane **21**) side in a region located at a depth of more than 10 nm from the upper surface (the second plane **22**) of the first electrode **20**. The impurity concentration can be changed in the thickness direction of the first electrode **20** by the condition such as energy when performing ion implantation.

Here, the impurity concentration can be estimated from the condition when performing ion implantation or the condition for annealing, and also can be measured by a secondary ion mass spectrometry (SIMS) or the like. The SIMS can perform measurement under the condition that, for example, the first electrode **20** is irradiated with 5 keV Cs as a primary ion from the side of the second plane **22**. By doing this, a concentration profile from the upper surface side to the lower surface side of the first electrode **20** can be obtained.

The phrase "the impurity concentration monotonically decreases" refers to that in the impurity concentration profile from the upper surface side to the lower surface side, the concentration decreases with no local maximum points or local minimum points. Incidentally, the maximum or the minimum of the concentration appearing in the profile due to the noise or the resolution when performing measurement by SIMS or the like shall be ignored.

The impurity concentration in the first electrode **20** monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode **20** as described above, however, in a region located at a depth of less than 10 nm from the upper surface of the first electrode **20**, the concentration profile may have a maximum or a local maximum.

The first electrode **20** is formed by, for example, depositing a polycrystalline silicon layer on the entire surface of the substrate **10** by a CVD (Chemical Vapor Deposition) method, a sputtering method, or the like, and thereafter patterning the layer by a photolithographic technique and an etching technique. Examples of the etching technique at this time include wet etching and dry etching. When dry etching is used, an effect of suppressing the formation of an angular portion on the first electrode **20** is prominent. The angular portion will be described in detail in "3. Experimental Examples".

In this embodiment, the etching rate is set higher in a region where the impurity concentration is higher, and the etching rate is set lower in a region where the impurity concentration is lower. That is, the impurity concentration is set higher and the etching rate is set higher on the upper surface side than on the lower surface side. According to this, the tapered shape is efficiently formed. The etching is preferably isotropic etching. One of the reasons is that a difference in lateral etching rate due to a difference in impurity concentration becomes prominent, and therefore, the tapered shape can be more

efficiently formed. Further, in order to increase the etching rate, an impurity having n-type conductivity may be used.

1.2 Second Electrode

The second electrode **30** is disposed above and spaced apart from the first electrode **20**. Further, the second electrode **30** can be deformed by an electrostatic force between the first electrode **20** and the second electrode **30**.

The second electrode **30** may have a portion formed on the substrate **10**. The shape of the second electrode **30** is not particularly limited, and is suitably designed according to the requirement for the function or sensitivity of the oscillator **100**. In the example shown in FIG. **2**, the second electrode **30** is formed in a rectangular shape so as to overlap with the first electrode **20** in plan view and electrically connected to an integrally formed wiring **44**.

The second electrode **30** has a facing plane **31** facing and spaced apart from the first electrode **20**. The facing plane **31** faces and is spaced apart from the second plane **22** and the tapered plane **23** of the first electrode **20**.

The thickness of the second electrode **30** can be set to, for example, 100 nm or more and 10 μ m or less. The function of the second electrode **30** in the oscillator **100** is to serve as one of the electrodes constituting a capacitor by being paired with the first electrode **20**.

The material of the second electrode **30** is not particularly limited as long as it has electrical conductivity, however, for example, one metal or an alloy of two or more metals selected from the group consisting of Cu, Au, Pt, Co, and Ni, or polycrystalline silicon doped with an impurity can be used. In the case of polycrystalline silicon, examples of the impurity include arsenic (As), phosphorus (P), and boron (B). The impurity can be introduced by, for example, ion implantation. The impurity may be activated by a heat treatment.

The second electrode **30** can be formed by, for example, forming a sacrificial layer on the first electrode **20**, depositing a layer made of a desired material on the sacrificial layer using a CVD method, a sputtering method, or the like, and thereafter patterning the layer using a photolithographic technique and an etching technique, followed by removing the sacrificial layer by etching. As such a sacrificial layer, oxide silicon or the like can be used, and in this case, the sacrificial layer may be formed by thermally oxidizing the polycrystalline silicon of the first electrode **20**. In the case where the sacrificial layer is formed by thermally oxidizing the polycrystalline silicon, the shape of the second plane **22** and the tapered plane **23** of the first electrode **20** is easily transferred to the facing plane **31** of the second electrode **30** with high followability, and therefore, an effect of this embodiment that the formation of a groove in the facing plane **31** of the second electrode **30** is suppressed is more prominent.

1.3. Operational Effect

In the oscillator **100** of this embodiment, grooves acting as stress concentration points are reduced on the surface of the second electrode **30** facing the first electrode **20**. That is, since the impurity concentration in the first electrode **20** monotonically decreases from the surface side to the depth direction in a region located at a depth of more than 10 nm from the surface of the first electrode **20**, when the first electrode **20** is formed, an angular portion is hardly formed on the first electrode **20**. Therefore, the shape of a groove corresponding to the angular portion on the first electrode **20** is hardly formed on the second electrode **30** formed to face the first electrode **20**. According to this, in the oscillator **100** of this embodiment, in the case where the second electrode **30** is deformed by an electrostatic force between the first electrode **20** and the second electrode **30**, stress concentration points on the second electrode **30** are reduced, and as a result, the second electrode

30 is hardly damaged, and thus, high reliability is provided. Further, the shape of a groove corresponding to an angular portion on the first electrode **20** is hardly formed on the second electrode **30** formed to face the first electrode **20**, and therefore, the first electrode **20** and the second electrode **30** hardly come into contact with each other, and thus, an effect of suppressing the occurrence of short circuit between the electrodes is high.

1.4. Method for Producing Oscillator

FIGS. **3** to **8** are each a schematic cross-sectional view showing each step of a method for producing an oscillator of this embodiment. The method for producing an oscillator according to this embodiment includes: (a) forming a first layer **20a** on a substrate **10**; (b) ion implanting a first impurity into a first region of the first layer **20a**; (c) forming a first electrode **20** having a tapered plane **23** on a side surface thereof by patterning the first layer **20a**; (d) forming a sacrificial layer **25** on the first electrode **20** and on the tapered plane **23** of the first electrode **20**; (e) forming a second electrode **30** on the substrate **10** and the sacrificial layer **25** so that the second electrode is disposed to face at least a part of the upper surface of the first electrode **20** and the tapered plane **23** of the first electrode **20**; and (f) removing the sacrificial layer **25**, wherein the step (b) is performed so that the concentration of the first impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode **20**.

Hereinafter, the steps of the method for producing an oscillator of this embodiment will be sequentially described.

First, a substrate **10** is prepared by forming an underlayer **12** on a silicon substrate **11**. The underlayer **12** is composed of, for example, silicon nitride, and can be formed by a CVD method or a sputtering method. Further, the underlayer **12** may be patterned as needed.

Subsequently, as shown in FIG. **3**, a first layer **20a** (in this embodiment, a polycrystalline silicon film is used) serving as a first electrode **20** is formed. The first layer **20a** can be formed by, for example, a CVD method, a sputtering method, or the like.

Subsequently, as shown in FIG. **4**, in a first region of the first layer **20a**, a first impurity is ion implanted (the arrows in the drawing conceptually show ion implantation). This step can be carried out by a widely used ion implantation method. The first region of the first layer **20a** may be the entire first layer **20a** in plan view or a part thereof as long as it is set in a region including a portion where a desired etching rate is obtained. In the example shown in the drawing, the first region is set to be the entire surface of the first layer **20a**. Further, as the first impurity, arsenic (As), phosphorus (P), boron (B), or the like can be used. By this step, the electrical conductivity can be given to the first layer **20a** (polycrystalline silicon), and the distribution of the concentration of the first impurity in the thickness direction of the first layer **20a** can be formed. The ion implantation in this step may be performed a plurality of times. Further, the conductivity types of impurities to be used for the ion implantation performed a plurality of times may be the same or different. Further, the conductivity type of the first impurity may be n-type.

In this step, the ion implantation is performed so that the concentration of the first impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first layer **20a**. Also in the case where the ion implantation is performed a plurality of times (for example, in the case where a first impurity and a second impurity are ion implanted), the ion implantation is performed so that the

combined concentration of the first impurity and the second impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first layer **20a**. After this step, before the step of forming the first electrode **20** by patterning the first layer **20a**, a heat treatment step may be included as needed. In this case, the condition for the ion implantation in this step and the condition for the heat treatment may be adjusted so that after performing the heat treatment step, the concentration of the impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first layer **20a**. In the case where the ion implantation is performed a plurality of times (for example, in the case where a first impurity and a second impurity are ion implanted), the heat treatment step may be performed between the step of ion implanting the first impurity and the step of ion implanting the second impurity. In this case, the condition for the ion implantation in this step and the condition for the heat treatment may be adjusted so that after the second impurity is ion implanted, the combined concentration of the first impurity and the second impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first layer **20a**.

Subsequently, as shown in FIGS. **5** and **6**, the first electrode **20** is formed by patterning the first layer **20a**. That is, as shown in FIG. **5**, a mask **M1** (for example, a resist pattern) is formed by a photolithographic technique, and then, as shown in FIG. **6**, the first layer **20a** is etched by using the mask **M1** as a mask, whereby the first electrode **20** is formed. The etching may be allowed to proceed on the lower surface side of the mask **M1**. In the example shown in the drawings, a wiring **42** is simultaneously formed in this step. By the etching, a tapered plane **23** of the first electrode **20** is formed.

The etching in this step can be performed by at least either dry etching or wet etching. In this step, since the concentration of the first impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first layer **20a**, an angular portion is hardly formed on the tapered plane **23** of the first electrode **20** and in the vicinity of a connection part between the tapered plane **23** and the second plane **22** of the first electrode **20**. Such a characteristic is particularly prominent when dry etching is adopted in this step. The angular portion will be described in detail in “3. Experimental Examples”.

Subsequently, as shown in FIG. **7**, a sacrificial layer **25** is formed on the first electrode **20**. In this embodiment, the sacrificial layer **25** is formed by thermally oxidizing the polycrystalline silicon of the first electrode **20**. The thermal oxidation treatment can be performed, for example, at a temperature of 800° C. or higher and 1100° C. or lower.

Subsequently, as shown in FIG. **8**, a second electrode **30** is formed on the substrate **10** and the sacrificial layer **25**. The second electrode **30** can be formed by, for example, depositing a layer made of a desired material using a CVD method, a sputtering method, or the like, and thereafter patterning the layer using a photolithographic technique and an etching technique. In the example shown in the drawings, a wiring **44** is simultaneously formed in this step.

Then, the sacrificial layer **25** is removed. The sacrificial layer **25** can be removed by, for example, wet etching using hydrofluoric acid, buffered HF (a mixed solution containing hydrofluoric acid and ammonium fluoride), or the like, dry etching using a gas such as hydrogen fluoride, or the like.

As described above, the oscillator **100** shown in FIG. **1** can be produced.

According to the method for producing an oscillator of this embodiment, an angular portion is hardly formed on the first electrode **20**, and therefore, a groove is hardly formed on the facing plane **31** of the second electrode **30** facing the first electrode **20**. Due to this, a highly reliable oscillator, in which the damage to the second electrode **30** which is deformed by an electrostatic force between the first electrode **20** and the second electrode **30** is suppressed, and also the occurrence of short circuit between the electrodes is suppressed can be produced. Further, according to the method for producing an oscillator of this embodiment, even in the case where the shape of the first electrode **20** is reflected in the shape of the second electrode **30** through the sacrificial layer **25**, a highly reliable oscillator can be produced.

2. Electronic Device

2.1. Electronic Device

An electronic device according to the invention includes the above-described oscillator. Hereinafter, an electronic device **200** including a substrate **10** and the above-described oscillator **100** accommodated in a hollow **1** formed on the substrate **10** will be described.

FIG. **9** is a schematic cross-sectional view showing the electronic device **200**. The oscillator **100** included in the electronic device **200** is the same as the above-described oscillator **100**, and therefore, the same reference numerals are assigned to the same members, and a detailed description thereof is omitted.

As shown in FIG. **9**, the electronic device **200** includes the substrate **10**, the hollow **1** formed on the substrate **10**, a lid **50** covering the hollow **1**, and the oscillator **1** disposed in the hollow **1**.

The substrate **10** has an underlayer **12** as shown in the drawing, which functions as an etching stopper layer when the hollow **1** is formed. Between the underlayer **12** and the substrate **10**, a trench insulating layer, an LOCOS (Local Oxidation of Silicon) insulating layer, a semi-recess LOCOS insulating layer, or the like (not shown in the drawing) may be formed.

The lid **50** is formed so as to cover the hollow **1**. The lid **50** may be composed of one member, but may be composed of a member having a through-hole and a member sealing the through-hole of the member having the through-hole. In the case where the lid **50** is composed of one member, the electronic device **200** may have other structures such as a hole for forming the hollow **1** by, for example, etching, and a sealing member. In the example shown in the drawing, the lid **50** is composed of a first sealing layer **54** having a through-hole **52** and a second sealing layer **56** laminated on the first sealing layer **54** and sealing the through-hole **52**.

The first sealing layer **54** has the through-hole **52**. The number of the through-holes **52** is not limited. The first sealing layer **54** can be configured to have a single layer structure, but may be configured to have, for example, a laminate structure of three or more layers, in which as the uppermost layer of the laminate structure, a layer composed of at least one substance selected from TiN, Ti, W, Au, and Pt, or an alloy made of these substances is used, and as the lowermost layer of the laminate structure, a layer composed of at least one substance selected from TiN, Ti, W, Au, and Pt, or an alloy of these substances is used, and at least one layer of the laminate structure is formed as an Al—Cu alloy layer.

The second sealing layer **56** is formed on the first sealing layer **54**. The second sealing layer **56** can close the through-

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hole **52** of the first sealing layer **54**. The second sealing layer **56** includes, for example, a layer composed of an alloy of one or more substances selected from the group consisting of Al, W, and Cu. The first sealing layer **54** and the second sealing layer **56** can function as the lid **50** which covers the hollow **1** from the above to seal the hollow **1**.

The hollow **1** is a space for accommodating the oscillator **100**. In the example shown in the drawing, the hollow **1** is defined by the underlayer **12**, an interlayer insulating layer **80**, and the lid **50**. The interior of the hollow **1** can be brought to, for example, a decompressed state, and by doing this, the operational accuracy of the oscillator **100** can be improved.

The oscillator **100** is disposed in the hollow **1**. The first electrode **20** and the second electrode **30** are connected to a wiring **42** and a wiring **44**, respectively, and further connected to a wiring **72** and a wiring **74** through a via **62** and a via **64** formed in the interlayer insulating layer **80**, respectively.

Although not shown in the drawing, the electronic device **200** may also include a circuit portion having a transistor or the like, a terminal for external connection, a pad, an insulating layer such as a passivation layer, or the like. Also, the electronic device **200** may have a WCSP structure.

2.2. Method for Producing Electronic Device

The electronic device of this embodiment can be produced as follows, for example.

A method for producing an electronic device **200** of this embodiment includes the method for producing an oscillator **100** described above. Therefore, a detailed description of the overlapping production steps is omitted. FIGS. **10** to **14** are each a schematic cross-sectional view showing each step of the method for producing an electronic device **200**.

The method for producing an electronic device **200** of this embodiment includes: forming an interlayer insulating layer **80** covering an oscillator **100**; forming a lid **50** covering the oscillator **100** and the interlayer insulating layer **80**; forming a through-hole **52** in the lid **50**; and forming a hollow **1** accommodating the oscillator **100** by removing the interlayer insulating layer **80** covering the oscillator **100** and a sacrificial layer **25** by etching through the through-hole **52**.

First, in the same manner as the above-described method for producing an oscillator **100**, a first electrode **20**, a sacrificial layer **25**, and a second electrode **30** are formed (see FIG. **8**). At this time, the oscillator **100** is not completed, however, the structure shown in FIG. **8** is sometimes referred to as the oscillator **100** in the description of this production method.

Subsequently, as shown in FIG. **10**, an interlayer insulating layer **80** covering the sacrificial layer **25** and the second electrode **30** is formed. The interlayer insulating layer **80** is formed by, for example, a CVD method, a coating (spin-coating) method, or the like. After forming the interlayer insulating layer **80**, a treatment of flattening the surface of the interlayer insulating layer **80** may be performed.

Subsequently, as shown in FIG. **11**, on a wiring **42** and a wiring **44**, a via **62** and a via **64** are formed, respectively, and a wiring **72** and a wiring **74** connected thereto are formed. The vias **62** and **64** can be formed by, for example, filling W, Al, or the like. Further, the wirings **72** and **74** can be formed by, for example, sputtering Al, Cu, W, or the like, followed by patterning. In addition, the interlayer insulating layer **80** may be further formed by the same step as described above. At this time, if necessary, a via and a wiring may be further formed. After forming the interlayer insulating layer **80**, a treatment of flattening the surface of the interlayer insulating layer **80** may be performed.

Subsequently, as shown in FIG. **12**, a first sealing layer **54** of a lid **50** is formed. The first sealing layer **54** can be formed by, for example, forming a film through a vapor-phase growth

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method such as a CVD method or a sputtering method, followed by patterning. Further, by this patterning, as shown in FIG. **12**, a through-hole **52** communicating with a hollow **1** is formed.

Subsequently, as shown in FIG. **13**, the interlayer insulating layer **80** and the sacrificial layer **25** present in a region to become the hollow **1** are removed by allowing an etching liquid or an etching gas to pass through the through-hole **52**, whereby the hollow **1** and the oscillator **100** are formed (in this specification, this step is sometimes referred to as "release step"). The release step can be performed by, for example, wet etching using hydrofluoric acid, buffered HF (a mixed solution containing hydrofluoric acid and ammonium fluoride), or the like, dry etching using a gas such as hydrogen fluoride, or the like. In the release step, a side wall that defines the side surface of the hollow **1** may be used, and in this case, for example, in the above-described step of forming the via **62** and the like, the side wall is formed simultaneously, and the resulting side wall may be used.

Thereafter, the hollow **1** is washed as needed. The washing can be performed with, for example, isopropyl alcohol (IPA) or water.

Then, as shown in FIG. **9**, a second sealing layer **56** is formed on the first sealing layer **54**. The second sealing layer **56** is formed by, for example, forming a film through a vapor-phase growth method such as a sputtering method or a CVD method, and can seal the through-hole **52**. Further, by forming the second sealing layer **56** by a vapor-phase growth method, also the hollow **1** can be sealed while keeping the interior of the hollow **1** in a decompressed state. The lid **50** may be patterned as needed.

By the steps illustrated above, the electron device **200** can be produced.

According to the method for producing an electronic device of this embodiment, an angular portion is hardly formed on the first electrode **20** of the oscillator **100**, and therefore, a groove is hardly formed on the plane of the second electrode **30** facing the first electrode **20**. Due to this, the electron device **200** including the highly reliable oscillator **100**, in which the damage to the second electrode **30** which is deformed by an electrostatic force between the first electrode **20** and the second electrode **30** is suppressed, and also the occurrence of short circuit between the electrodes is suppressed can be produced.

3. EXPERIMENTAL EXAMPLES

Hereinafter, the present invention will be described in further detail by showing experimental examples, however, the invention is by no means limited to the following experimental examples.

3.1. Experimental Method

A plurality of samples in which a polycrystalline silicon film was formed by a CVD method on a silicon substrate having an underlayer (Si_3N_4) formed thereon were prepared. The thickness of the polycrystalline silicon film at this time was 280 nm in each sample.

Phosphorus (P) was implanted as an impurity into the entire surface of the polycrystalline silicon film. As for the conditions for the ion implantation and the heat treatment, the following five different types of conditions were employed for each sample.

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Experimental Example 1

ion implantation (acceleration voltage: 35 keV, dose: 6E15 atoms/cm²)

Experimental Example 2

ion implantation (acceleration voltage: 35 keV, dose: 6E15 atoms/cm²), followed by ion implantation (acceleration voltage: 5 keV, dose: 6E15 atoms/cm²)

Experimental Example 3

ion implantation (acceleration voltage: 5 keV, dose: 6E15 atoms/cm²)

Experimental Example 4

ion implantation (acceleration voltage: 35 keV, dose: 6E15 atoms/cm²), followed by heat treatment (650° C., 20 minutes, in nitrogen atmosphere)

Experimental Example 5

ion implantation (acceleration voltage: 35 keV, dose: 6E15 atoms/cm²), followed by heat treatment (650° C., 20 minutes, in nitrogen atmosphere), and further followed by ion implantation (acceleration voltage: 5 keV, dose: 6E15 atoms/cm²)

The surface of each sample was measured by SIMS, and the phosphorus concentration distribution in the thickness direction was determined. The results are shown in FIG. 14. The measurement by SIMS was performed under the condition that the surface was irradiated with 5 keV Cs as a primary ion.

Thereafter, on each sample, a mask pattern was formed, followed by dry etching. Then, the mask was removed, a protective film for cross-sectional observation was formed on the polycrystalline silicon film, whereby a sample of each experimental example was obtained.

Each of the obtained samples was cut and the cut surface was observed by a scanning electron microscope (SEM). The results are shown in FIG. 15.

3.2. Experimental Results

As is shown in FIGS. 14 and 15, it was found that there is a very good correlation between the concentration profile obtained by SIMS and the shape of the edge of the polycrystalline silicon film obtained from the SEM observation. The SEM images in FIG. 15 are shown in such a manner that the right side is the substrate side.

In the concentration profile obtained by SIMS shown in FIG. 14, in the case of the samples of the experimental examples 1, 2, and 4, there was a local maximum point in a region located at a depth of 40 to 50 nm from the surface. In the SEM images shown in FIG. 15 corresponding thereto, in the case of the samples of the experimental examples 1, 2, and 4, an angular portion protruding toward the surface side of the sample was observed. On the other hand, in the case of the samples of experimental examples 3 and 5, in the concentration profile obtained by SIMS, the concentration of phosphorus monotonically decreased in a region located at a depth of more than 10 nm from the surface without having a local maximum, and a marked angular portion was not observed in the SEM images corresponding thereto. Further, although not shown in the drawing, in the concentration profiles obtained

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by SIMS of the samples of the experimental examples 2, 3, and 5, a peak was observed in a region located at a depth of about 5 nm from the surface.

From these results, it was found that in the case where the impurity concentration monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the polycrystalline silicon film, even if there is a maximum or a local maximum in the concentration profile in a region located at a depth of less than 10 nm from the upper surface, an angular portion is not observed.

Accordingly, it will be understood that in the case where an additional layer is laminated on the polycrystalline silicon film of the experimental example 3 or 5, a groove (dent) is hardly formed on a plane of the additional layer facing the polycrystalline silicon film.

Note that in the invention, when it is described that a specific member B is disposed (or formed) on (or under) a specific member A, it is not limited to an embodiment in which the member B is disposed (or formed) directly on (or under) the member A, but includes an embodiment in which the member B is disposed (or formed) directly on (or under) the member A through another member within the scope in which the operational effect of the invention is not deteriorated.

The invention is not limited to the embodiments described above, and various modifications are possible. For example, the invention includes essentially the same configurations as the configurations described in the embodiments (for example, a configuration in which the functions, methods, and results are the same, or a configuration in which the objects and the effects are the same). Further, the invention also includes configurations in which non-essential portions of the configurations described in the embodiments are substituted. Further, the invention includes configurations demonstrating the same operational effects or configurations achieving the same objects as the configurations described in the embodiments. Further, the invention includes configurations in which known technologies are added to the configurations described in the embodiments.

What is claimed is:

1. A method for producing an oscillator, comprising:

- (a) forming a first layer on a substrate;
- (b) ion implanting a first impurity into a first region of the first layer;
- (c) forming a first electrode having a tapered plane on a side surface thereof by patterning the first layer;
- (d) forming a sacrificial layer on the first electrode and on the tapered plane of the first electrode;
- (e) forming a second electrode on the substrate and the sacrificial layer so that the second electrode is disposed to face at least a part of the upper surface of the first electrode and the tapered plane of the first electrode; and
- (f) removing the sacrificial layer, wherein the step (b) is performed so that the concentration of the first impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode.

2. The method for producing an oscillator according to claim 1, further comprising (g) ion implanting a second impurity into a second region of the first layer between the step (a) and the step (b), or between the step (b) and the step (c), wherein

the step (g) is performed so that the second region is located closer to the substrate than the first region,

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at least a part of the second region overlaps with the first region, and

the combined concentration of the first impurity and the second impurity monotonically decreases from the upper surface side to the lower surface side in a region located at a depth of more than 10 nm from the upper surface of the first electrode.

3. The method for producing an oscillator according to claim 1, further comprising, between the step (a) and the step (b), or between the step (b) and the step (c): (g) ion implanting a second impurity into a second region of the first layer; and (h) heating the first layer, wherein

the step (g) is performed so that the second region is located closer to the substrate than the first region,

the step (h) is performed so that at least a part of the second impurity is diffused in the first region, and

the step (g) and the step (h) are performed so that the combined concentration of the first impurity and the second impurity monotonically decreases from the upper surface side to the lower surface side in a region

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located at a depth of more than 10 nm from the upper surface of the first electrode.

4. The method for producing an oscillator according to claim 1, wherein the first impurity and the second impurity have the same conductivity type.

5. The method for producing an oscillator according to claim 1, wherein the first layer is composed of a semiconductor layer, and

in the step of forming the sacrificial layer, the semiconductor layer is formed by thermal oxidation.

6. The method for producing an oscillator according to claim 5, wherein the first layer is composed of a polycrystalline silicon layer.

7. The method for producing an oscillator according to claim 1, wherein the step of patterning the first layer includes:

forming a resist pattern on the first layer; and

etching the first layer by using the resist pattern as a mask, and

in the etching step, etching is allowed to proceed on the lower surface side of the resist pattern.

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